

4-Lines, Uni-directional, Ultra-low Capacitance Transient Voltage Suppressors

Descriptions

The AZ1345-04F is an ultra-low capacitance TVS (Transient Voltage Suppressor) array designed to protect high speed data interfaces. It has been specifically designed to protect sensitive electronic components which are connected to data and transmission lines from over-stress caused by ESD (Electrostatic Discharge).

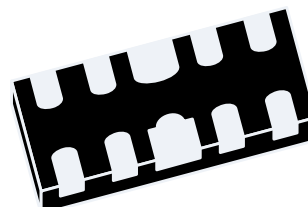
The AZ1345-04F incorporates four pairs of ultra- low capacitance steering diodes plus a TVS diode.

The AZ1345-04F may be used to provide ESD protection up to $\pm 20\text{kV}$ (contact discharge) according to IEC61000-4-2, and withstand peak pulse current up to 4A (8/20 μs) according to IEC61000-4-5.

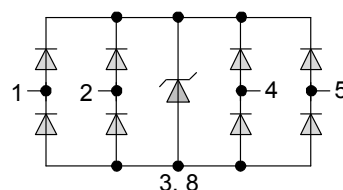
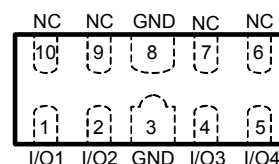
The AZ1345-04F is available in DFN2510-10L package. Standard products are Pb-free and Halogen-free.

Order information

Device	Package	Shipping
AZ1345-04F	DFN2510-10L	3000/Tape&Reel



DFN2510-10L (Bottom view)



Pin configuration (Top view)

Absolute maximum ratings

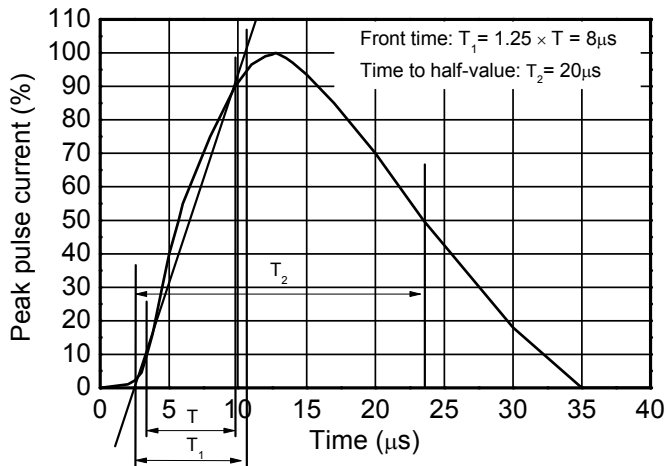
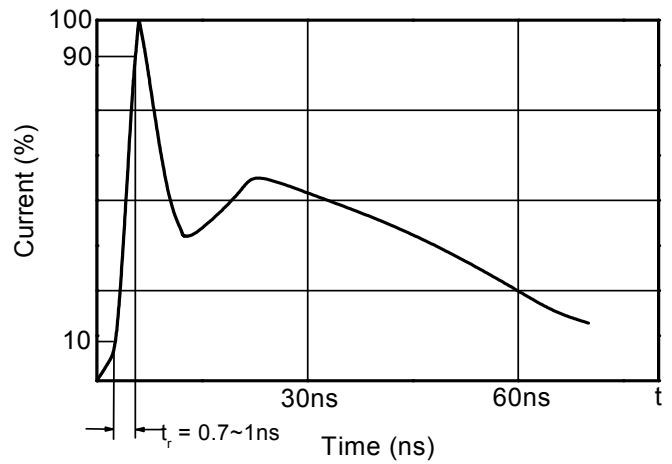
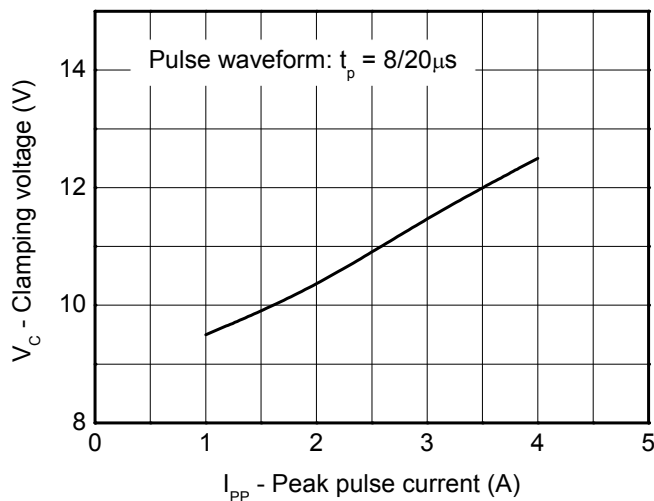
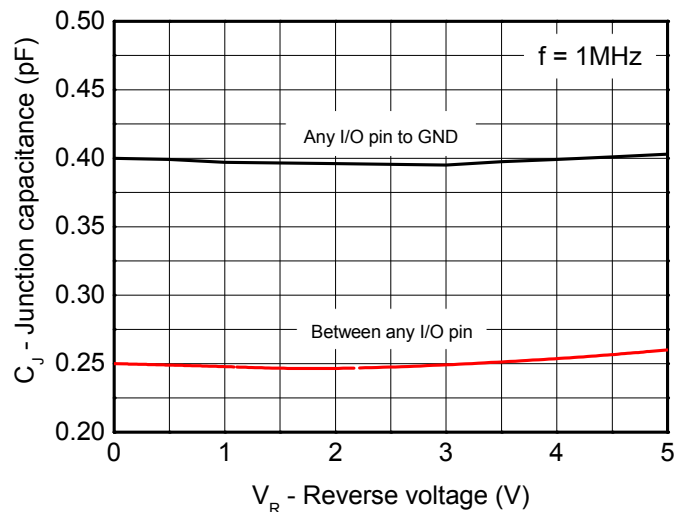
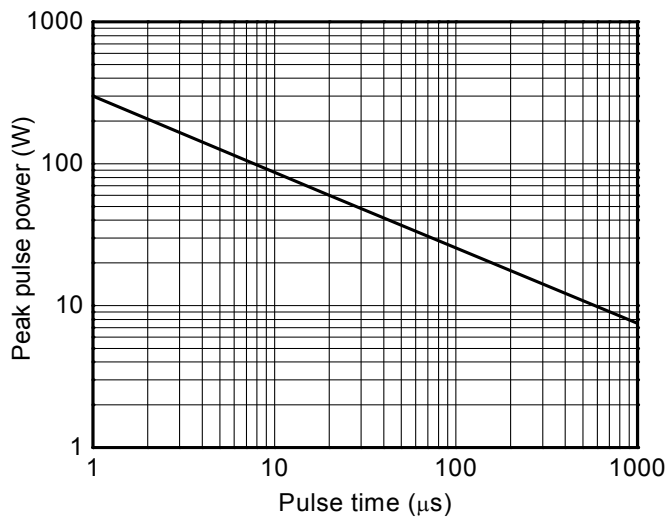
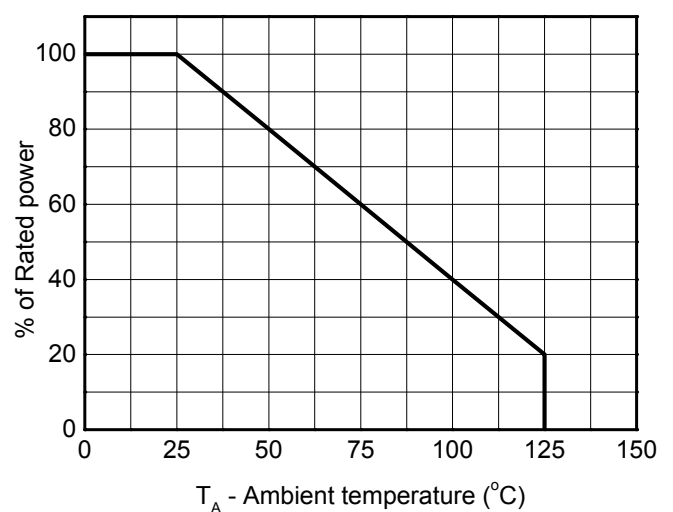
Parameter	Symbol	Rating	Unit
Peak pulse power ($t_p = 8/20\mu s$)	P_{pk}	60	W
Peak pulse current ($t_p = 8/20\mu s$)	I_{PP}	4	A
ESD according to IEC61000-4-2 air discharge	V_{ESD}	± 20	kV
ESD according to IEC61000-4-2 contact discharge		± 20	
Operation junction temperature	T_J	125	$^{\circ}C$
Lead temperature	T_L	260	$^{\circ}C$
Storage temperature	T_{STG}	-55~150	$^{\circ}C$

Electrical characteristics ($T_A = 25^{\circ}C$, unless otherwise noted)

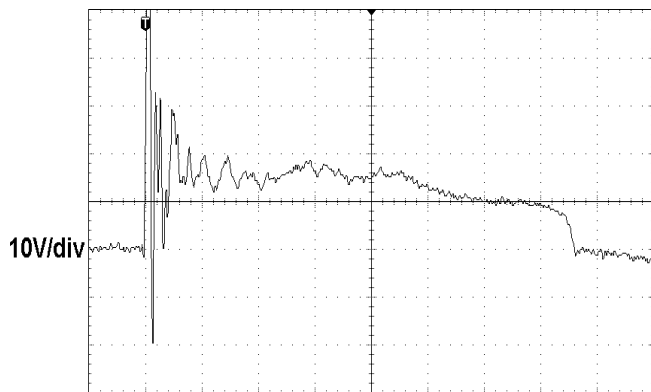
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse maximum working voltage	V_{RWM}				5.0	V
Reverse leakage current	I_R	$V_{RWM} = 5V$		<1	100	nA
Reverse breakdown voltage	V_{BR}	$I_T = 1mA$	7.0	8.0	9.0	V
Forward voltage	V_F	$I_T = 10mA$	0.6	0.9	1.2	V
Clamping voltage ¹⁾	V_{CL}	$I_{PP} = 16A, t_p = 100ns$		19.0		V
Dynamic resistance ¹⁾	R_{DYN}			0.65		Ω
Clamping voltage ²⁾	V_{CL}	$I_{PP} = 1A, t_p = 8/20\mu s$			11	V
		$I_{PP} = 4A, t_p = 8/20\mu s$			15	V
Junction capacitance	C_J	$V_R = 0V, f = 1MHz$ Any I/O pin to GND		0.40	0.65	pF
		$V_R = 0V, f = 1MHz$ Between any I/O pin		0.25	0.40	pF

Notes:

- 1) TLP parameter: $Z_0 = 50 \Omega$, $t_p = 100ns$, $t_r = 2ns$, averaging window from 60ns to 80ns. R_{DYN} is calculated from 4A to 16A.
- 2) Non-repetitive current pulse, according to IEC61000-4-5.

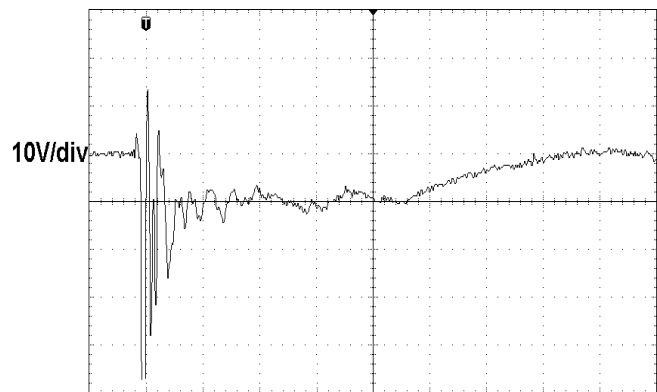
Typical characteristics ($T_A = 25^\circ\text{C}$, unless otherwise noted)

8/20 μs waveform per IEC61000-4-5

Contact discharge current waveform per IEC61000-4-2

Clamping voltage vs. Peak pulse current

Capacitance vs. Reverses voltage

Non-repetitive peak pulse power vs. Pulse time

Power derating vs. Ambient temperature

Typical characteristics ($T_A = 25^\circ\text{C}$, unless otherwise noted)



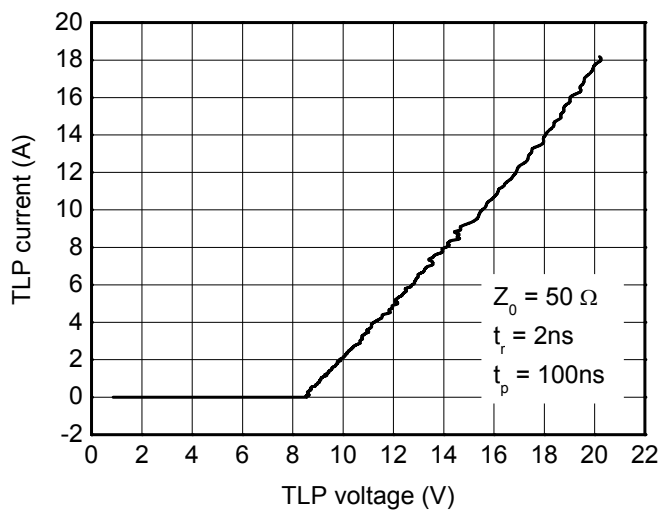
ESD clamping

(+8kV contact discharge per IEC61000-4-2)



ESD clamping

(-8kV contact discharge per IEC61000-4-2)



TLP Measurement